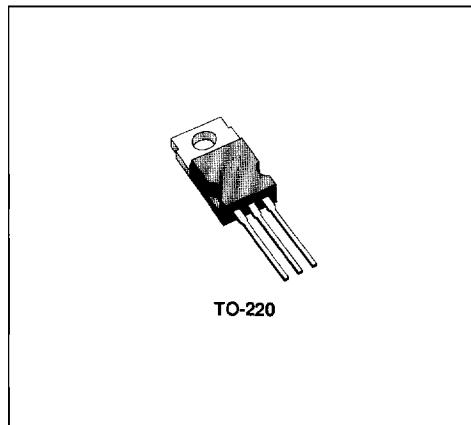


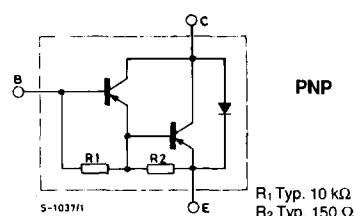
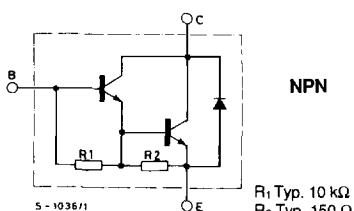
NPN/PNP POWER DARLINGTONS

DESCRIPTION

The BDW93, BDW93A, BDW93B and BDW93C are silicon epitaxial-base NPN transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package. They are intended for use in power linear and switching applications. The complementary PNP types are the BDW94, BDW94A, BDW94B and BDW94C respectively.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	NPN PNP*	Value				Unit
			BDW93 BDW94	BDW93A BDW94A	BDW93B BDW94B	BDW93C BDW94C	
V _{CBO}	Collector-base Voltage ($I_E = 0$)		45	60	80	100	V
V _{CEO}	Collector-emitter Voltage ($I_B = 0$)		45	60	80	100	V
I _C	Collector Current				12		A
I _{CM}	Collector Peak Current				15		A
I _B	Base Current				0.2		A
P _{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$				80		W
T _{stg}	Storage Temperature				− 65 to 150		°C
T _j	Junction Temperature				150		°C

* For PNP types voltage and current values are negative.

THERMAL DATA

R _{th} j case	Thermal Resistance Junction-case	Max	1.56	°C/W
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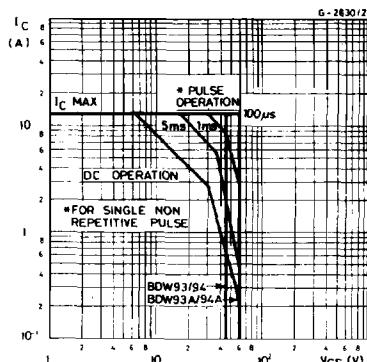
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cutoff Current (I _E = 0)	for BDW93/94 V _{CB} = 45 V for BDW93A/94A V _{CB} = 60 V for BDW93B/94B V _{CB} = 80 V for BDW93C/94C V _{CB} = 100 V T _{case} = 150 °C for BDW93/94 V _{CB} = 45 V for BDW93A/94A V _{CB} = 60 V for BDW93B/94B V _{CB} = 80 V for BDW93C/94C V _{CB} = 100 V			100 100 100 100 5	μA μA μA μA mA
I _{CEO}	Collector Cutoff Current (I _B = 0)	for BDW93/94 V _{CE} = 40 V for BDW93A/94A V _{CE} = 60 V for BDW93B/94B V _{CE} = 80 V for BDW93C/94C V _{CE} = 80 V			1 1 1 1	mA mA mA mA
I _{EBO}	Emitter Cutoff Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)} *	Collector-emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	45 60 80 100			V V V V
V _{C E(sat)} *	Collector-emitter Saturation Voltage	I _C = 5 A I _C = 10 A	I _B = 20 mA I _B = 100 mA		2 3	V V
V _{BE(sat)} *	Base-emitter Saturation Voltage	I _C = 5 A I _C = 10 A	I _B = 20 mA I _B = 100 mA		2.5 4	V V
h _{FE} *	DC Current Gain	I _C = 3 A I _C = 5 A I _C = 10 A	V _{CE} = 3 V V _{CE} = 3 V V _{CE} = 3 V	1000 750 100	20000	
V _F *	Parallel-diode Forward Voltage	I _F = 5 A I _F = 10 A			1.3 1.8	V V
h _{fe}	Small Signal Current Gain	I _C = 1 A f = 1 MHz	V _{CE} = 10 V	20		

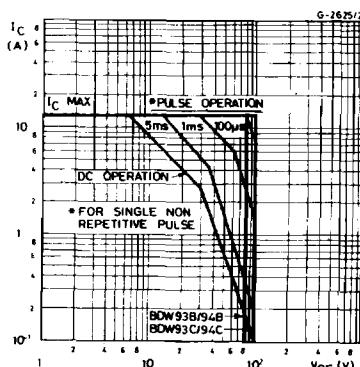
* Pulsed : pulse duration = 300 μs, duty cycle = 1.5 %.

For PNP types voltage and current values are negative.

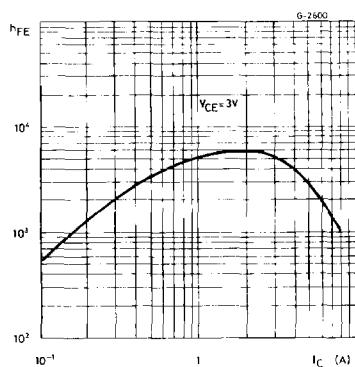
Safe Operating Areas (for **BDW93**, **BDW93A**,
BDW94, **BDW94A**).



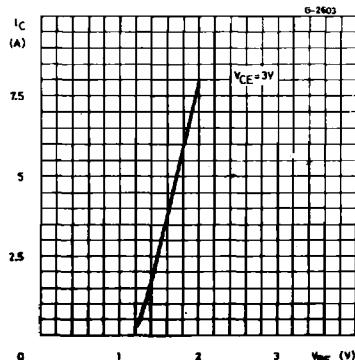
Safe Operating Areas (for **BDW93B**, **BDW93C**,
BDW94B, **BDW94C**).



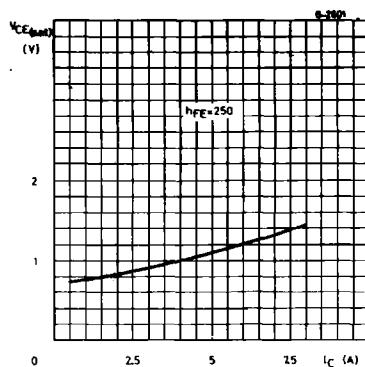
DC Current Gain (NPN types).



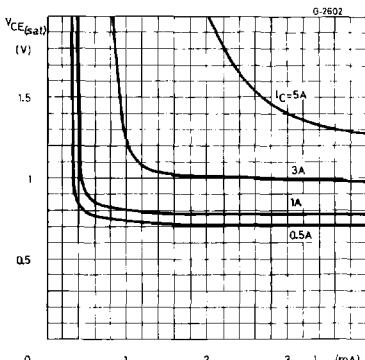
DC Transconductance (NPN types).



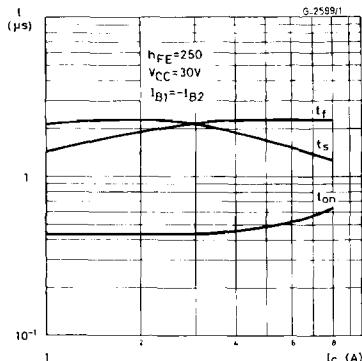
Collector-emitter Saturation Voltage (NPN types).



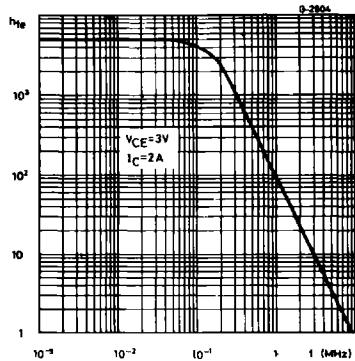
Collector-emitter Saturation Voltage (NPN types).



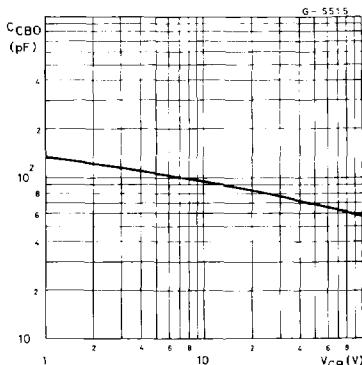
Saturated Switching Characteristics (NPN types).



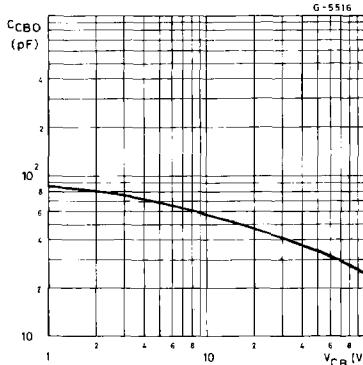
Small Signal Current Gain (NPN types).



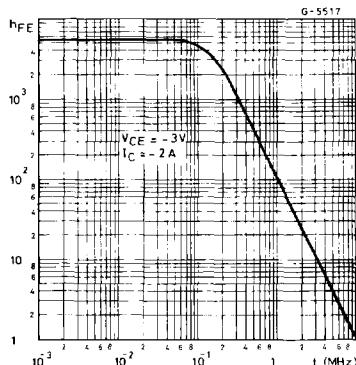
Collector-base Capacitance (PNP types).



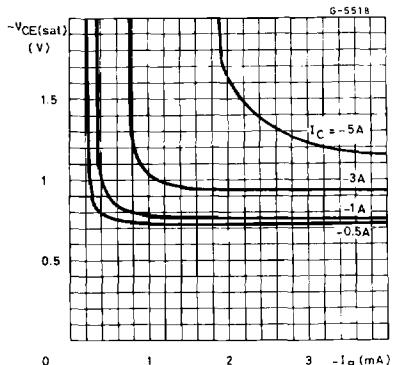
Collector-base Capacitance (NPN types).



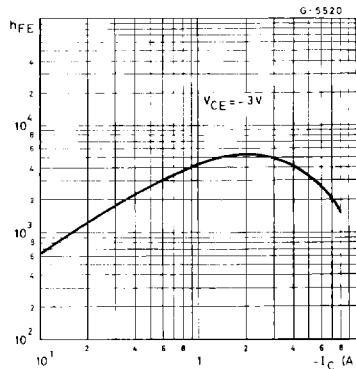
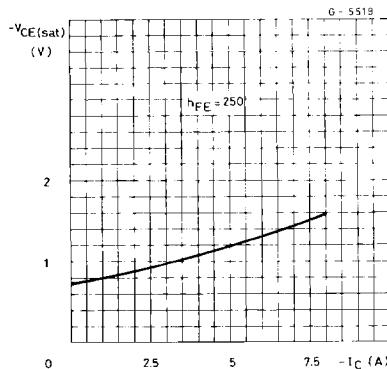
Small Signal Current Gain (PNP types).



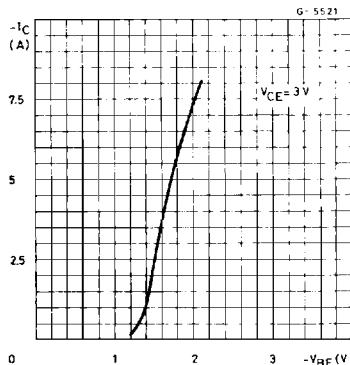
Collector-emitter Saturation Voltage (PNP types).



Collector-emitter Saturation Voltage (PNP types).



DC Transconductance (PNP types).



Saturated Switching Characteristics (PNP types).

